## **CLAIMS**

- A method of fabricating a radiation detector array comprising the steps of:
- a) providing on one face of a layer of material, an array of detector elements;
- b) forming an array of cavities in the layer of material such that each detector is positioned at the base of a cavity; and
- c) bonding the array of cavities and detectors to a silicon integrated circuit including a corresponding array of amplifiers and multiplex switches.
- 2. A method as claimed in claim 1 in which the layer of material is a silicon wafer and the cavities are formed by etching the wafer.
- 3. A method as claimed in claim 2, in which the etching process is deep reactive ion etching.
- 4. A method as claimed in claim 1 in which a profiled polymer mask is used to define the array of cavities.
- 5. A method as claimed in claim 1 comprising the further step of at least partially coating the cavities with metal.
- 6. A method as claimed in claim 5, in which the metal is sputtered onto the cavities.
- 7. A method as claimed in claim 5, in which the metal is evaporated onto the cavities.
- 8. A method as claimed in claim 1 including the further step of wholly or partially filling the cavities with dielectric material of refractive index higher than air.

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- A method of fabricating a radiation detector array comprising the steps of: 9.
- forming an array of cavities in a layer of material; a)
- providing, on one face of the material, an array of detector elements such that b) one element is positioned at the base of each cavity; and
- bonding the array of cavities and detectors to a silicon integrated C) circuit including a corresponding array of amplifiers and multiplex switches.
- A method as claimed in claim 9 in which the layer of material is a silicon wafer 10. and the cavities are formed by etching the wafer.
- A method as claimed in claim 10, in which the etching process is deep 11. reactive ion etching.
- A method as claimed in claim 9 in which a profiled polymer mask is used to 12. define the array of cavities.
- A method as claimed in claim 9 comprising the further step of at least partially 13. coating the cavities with metal.
- A method as claimed in claim 13, in which the metal is sputtered onto the 14. cavities.
- A method as claimed in claim 13, in which the metal is evaporated onto the 15. cavities.
- A method as claimed in claim 9 including the further step of wholly or partially 16. filling the cavities with dielectric material of refractive index higher than air.

- 17. A radiation detector array comprising an array of radiation collector cavities formed in a layer of material, each cavity having a detector element at its base, wherein the array of cavities and detectors is bonded to a silicon integrated circuit including a corresponding array of amplifiers and multiplex switches.
- 18. An array as claimed in claim 17, in which the detector elements are infrared detector elements.
- 19.) An array as claimed in claim 17 in which the cavities are shaped so as to have a gradually reducing cross sectional area from their openings towards their bases. Fig. 2-3
- 20. An array as claimed in claim 19, in which the cavities are conical.
- 21. An array as claimed in claim 19, in which the inner surfaces of the cavities are parabolic in shape.
- 22. An array as claimed in claim 21, in which the detectors are positioned at the foci of the parabolas.
- 23. An array as claimed in claim 17 wherein the pyroelectric detectors-are made from a thin film of a material that is substantially lead zirconate titanate.
- 24. An array as claimed in claim 17 wherein the detectors are made from a thin film of a material that is substantially lead scandium tantalate.
- 25. An array as claimed in claim 17 wherein the detectors are made from a thin film of a material that is substantially a copolymer of polyvinylidene fluoride and trifluoroethylene.
- 26. An array as claimed in claim 17, wherein the array is bonded using conductive bumps are made of silver loaded epoxy.



detector elements.

